

PATENT
Attorney Docket No.: AMAT/5975.P1/CPI/COPPER/BG
Express Mail No.: EV351031212US

ABSTRACT OF THE DISCLOSURE

A method of ruthenium layer formation for high aspect ratios, interconnect features is described. The ruthenium layer is formed using a cyclical deposition process. The cyclical deposition process comprises alternately adsorbing a ruthenium-containing precursor and a reducing gas on a substrate structure. The adsorbed ruthenium-containing precursor reacts with the adsorbed reducing gas to form the ruthenium layer on the substrate.

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